Claims 23-26 are cancelled.

27. (Amended) A gate stack, comprising:

a polysilicon layer over a semiconductive substrate;

a gate oxide layer on the polysilicon layer;

a metal silicide layer on the gate oxide layer;

a layer comprising $Si_xN_yO_z$:H over and in physical contact with the metal silicide, wherein x is from 0.39 to 0.65, y is from 0.02 to 0.56, and z is from 0.05 to 0.33; and

a silicon nitride layer on the layer comprising $Si_xN_yO_z$:H.

Claims 28-32 are cancelled.

33. (Amended) The gate stack of Claim 27, where the layer comprising $Si_xN_yO_z$:H has a thickness of from about 250Å to about 650Å.

Claims 34-35 are cancelled.

36. (New) The gate stack of claim 27 wherein y is from 0.02 to less than 0.1.

37. (New) The gate stack of claim 27 wherein x=0.5, y=0.37 and z=0.13.